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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-1EFU06-M3/I</u>

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Datasheet of VS-1EFU06-M3/I - DIODE ULT FAST 1A 600V DO219AB

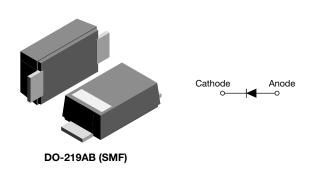
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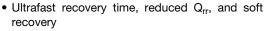
Vishay Semiconductors

Ultrafast Rectifier, 1 A FRED Pt®



PRODUCT SUMMARY				
Package	DO-219AB (SMF)			
I _{F(AV)}	1 A			
V_{R}	600 V			
V _F at I _F	0.83 V			
t _{rr}	55 ns			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES





• 175 °C maximum operating junction temperature

• For PCF CRM, snubber operation

Low forward voltage drop

Low leakage current

HALOGEN FREE

• Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art ultrafast recovery rectifiers designed with optimized performance of forward voltage drop, ultrafast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in PFC, boost, lighting, in the AC/DC section of SMPS, freewheeling and clamp

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V_{RRM}		600	V	
Average rectified forward current	I _{F(AV)}	T _C = 158 °C ⁽¹⁾	1	٨	
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C, 6 ms square pulse	30	А	
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +175	°C	

(1) Device on PCB with 8 mm x 16 mm soldering lands

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	$I_R = 100 \mu A$	600	-	-	
Forward voltage	V _F	I _F = 1 A	-	1.0	1.2	V
		I _F = 1 A, T _J = 150 °C	-	0.83	1	
Reverse leakage current	_	$V_R = V_R$ rated	-	-	3	
	I _R	T _J = 150 °C, V _R = V _R rated	-	20	100	μΑ
Junction capacitance	C _T	V _R = 600 V	-	5	-	pF

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 50 A$	Vμs, V _R = 30 V	-	42	-	
Develope ve enver time		I _F = 0.5 A, I _R = 1 A, I _{rr}	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	55	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	32	-	ns
		T _J = 125 °C		-	47	-	
Dook recovery current	ak recovery current I _{RRM}	T _J = 25 °C	$I_F = 1 A$ $dI_F/dt = 500 A/\mu s$ $V_R = 400 V$	-	4.8	-	Α
reak recovery current				6.8	-	A	
D	T _J = 25 °C		-	77	-		
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	160	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C
Thermal resistance, junction to case	R _{thJC}	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	15	°C/W
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	130	°C/W
Approximate weight				0.015		g
Approximate weight				0.0005		OZ.
Marking device		Case style DO-219AB (SMF)		MI	VU	

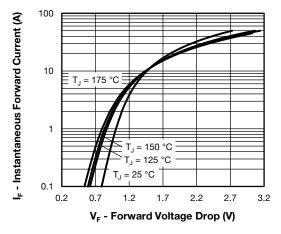


Fig. 1 - Typical Forward Voltage Drop Characteristics

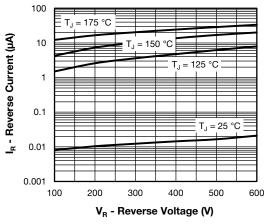


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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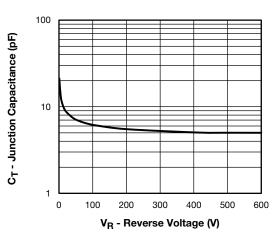


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

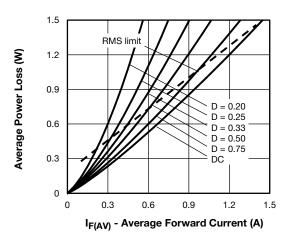


Fig. 5 - Forward Power Loss Characteristics

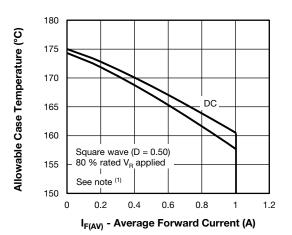


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

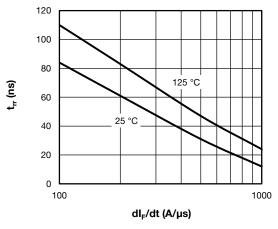


Fig. 6 - Typical Reverse Recovery Time vs. dI_{F}/dt

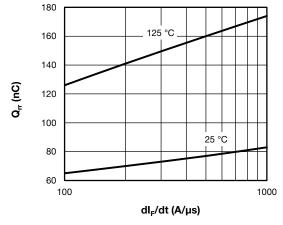


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

 $^{(1)}$ Formula used: $T_C = T_J$ - (Pd + Pd_{REV}) x R_{th,JC}; Pd = Forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 5); Pd_{REV} = Inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = rated V_R

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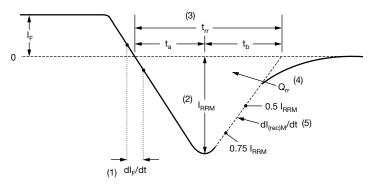
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- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

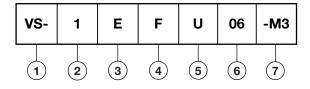
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- Current rating (1 = 1 A)
- 3 Circuit configuration:

E = single diode

4 - F = SMF package

5 - Process type,

U = ultrafast recovery

Voltage code (06 = 600 V)

7 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-1EFU06-M3/I	10 000	10 000	13"diameter plastic tape and reel		

LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95572		
Part marking information	www.vishay.com/doc?95618		
Packaging information	www.vishay.com/doc?95577		
SPICE model	www.vishay.com/doc?95639		

Revision: 22-Jan-16 4 Document Number: 95864

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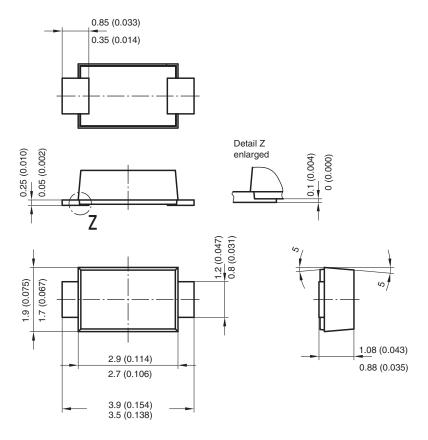


Outline Dimensions

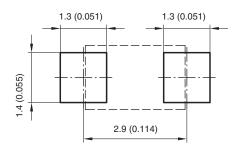
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DO-219AB (SMF)

DIMENSIONS in millimeters (inches)



Foot print recommendation:



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